

### END-LOOK PACKAGE PIN PHOTO DIODE

#### ● Features

1. Wide receiving angle
2. Linear response vs. irradiance
3. Fast switching time
4. End-looking Package ideal for space limited applications
5. Lens Appearance: Water Clear.
6. This product doesn't contain restriction substance, comply ROHS standard

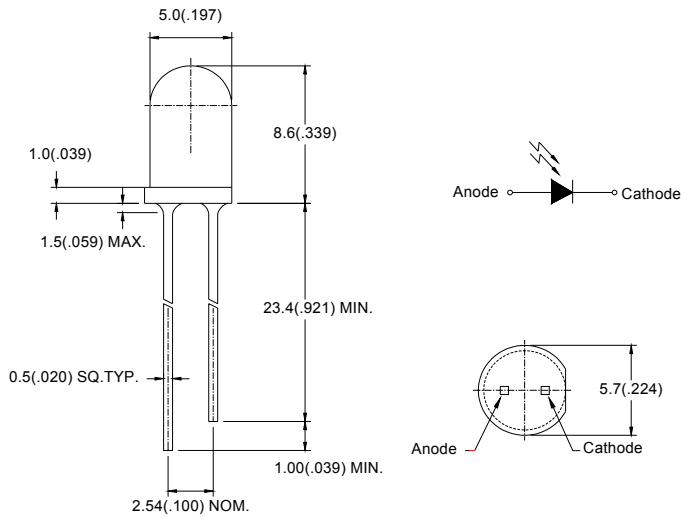
#### ● Description

The BPD-BQB334 device consists of a PIN silicon photodiode molded in a clear epoxy package which allows spectral response from visible to infrared light wavelengths. The wide receiving angle provides relatively even reception over a large area. The end-looking package is designed for easy PC board mounting. This photodiode is mechanically and spectrally matched to BRIGHT's GaAs and GaAlAs series of infrared emitting diodes.

#### ● Absolute Maximum Ratings(Ta=25°C)

| Parameter                  | Maximum Rating      | Unit |
|----------------------------|---------------------|------|
| Power Dissipation          | 100                 | mW   |
| Reverse Breakdown Voltage  | 60V                 |      |
| Operating Temperature      | -45°C ~ +85°C       |      |
| Storage Temperature Range  | -45°C ~ +100°C      |      |
| Lead Soldering Temperature | 260°C for 5 seconds |      |

#### ● Package Dimensions:



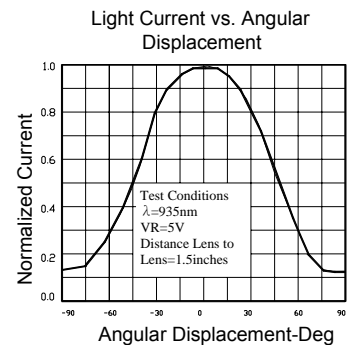
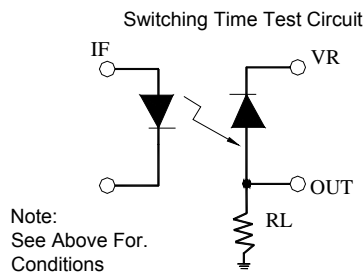
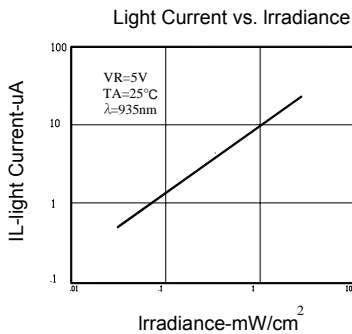
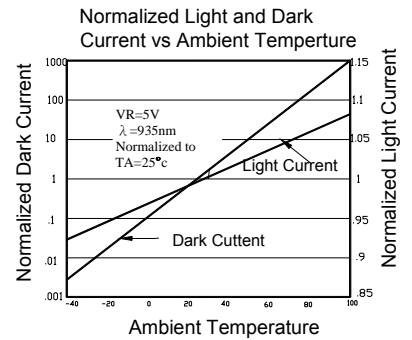
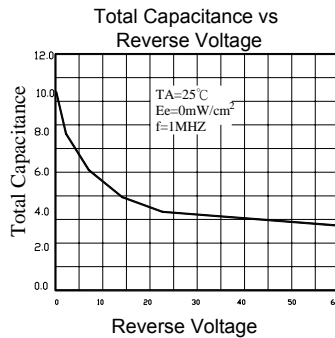
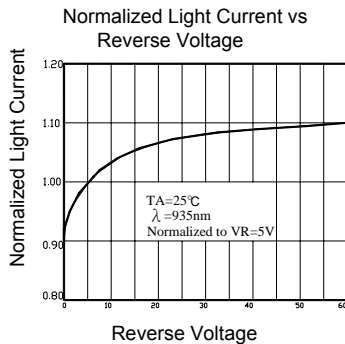
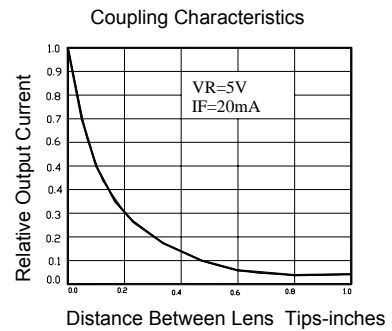
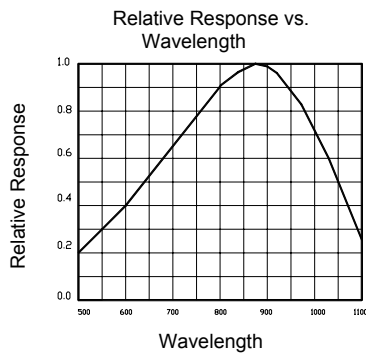
#### NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is  $\pm 0.25$ mm (0.01") unless otherwise specified.
3. Lead spacing is measured where the leads emerge from the package
4. Specifications are subject to change without notice

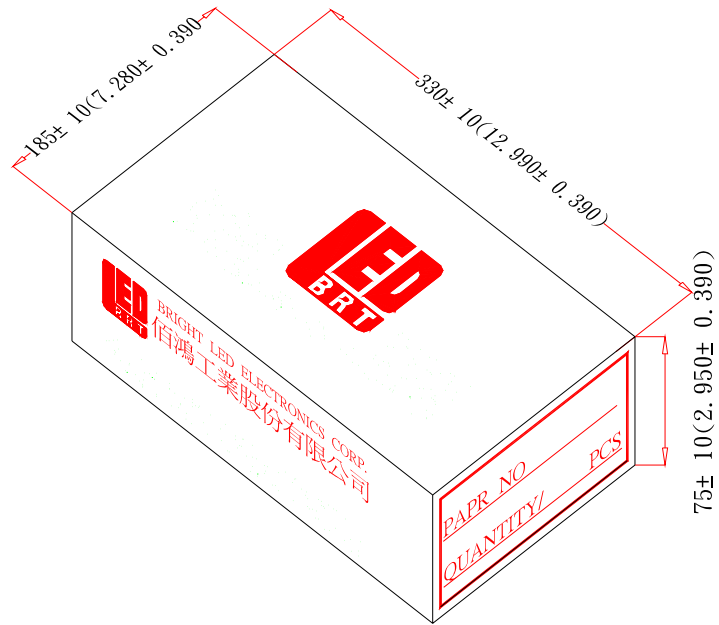
● **Electrical Characteristics** (TA=25°C unless otherwise noted)

| PARAMETER                  | SYM BOL    | MIN | TYP | MAX | UNITS   | TEST CONDITIONS                       |
|----------------------------|------------|-----|-----|-----|---------|---------------------------------------|
| Reverse Light Current      | $I_L$      | -   | 50  | -   | $\mu A$ | $V_R=5V, E_e=1mW/cm^2$                |
| Reverse Dark Current       | $I_D$      | -   | -   | 30  | nA      | $V_R=10V, E_e=0 mW/cm^2$              |
| Reverse Break down Voltage | $V_{(BR)}$ | 30  | -   | -   | V       | $I_R=100\mu A$                        |
| Forward Voltage            | $V_F$      | -   | -   | 1.2 | V       | $I_F=1mA$                             |
| Total Capacitance          | $C_T$      | -   | 21  | -   | PF      | $V_R=4V, E_e=0, f=1.0MHZ$             |
| Rise Time/ Fall Time       | tr/ tf     | -   | 40  | -   | ns      | $V_R=20V, \lambda=850nm, RL=50\Omega$ |

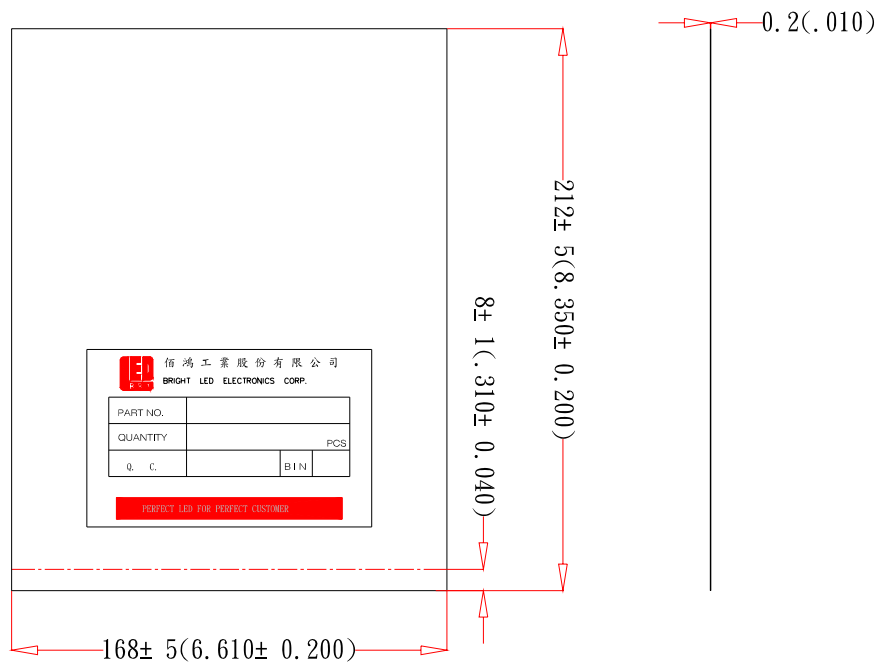
● **Typical Optical-Electrical Characteristic Curves**



● Tapping and packaging specifications(Units: mm)



● Packaging Bag Dimensions



**Notes:**

- 1、500pcs per bag,5Kpcs per box.
- 2、All dimensions are in millimeters(inches).
- 3、Specifications are subject to change without notice.